

isc Silicon NPN Power Transistor

DESCRIPTION

- · Low collector saturation voltage
- High DC current gain
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

 This transistor is ideal for audio frequency amplifier and switching especially in hybrid integrated circuits

pin 1.Base 2.Collector 3.Emitter TO-251 package

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	5	А
Ісм	Collector Current-Peak NOTE1	7	A
Pc	Collector Power Dissipation @Ta=25°C NOTE2	2	W
Тл	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$

NOTE1:PW≤300ms,Duty cycle ≤10% NOTE2:Printing boarding mounted

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DIM	m MIN	MAX
DIM A	MIN 6.40	MAX 6.48
DIM A B	MIN 6.40 5.10	MAX 6.48 5.50
DIM A B	MIN 6.40	MAX 6.48 5.50 6.20
DIM A B	MIN 6.40 5.10 5.80 9.20	MAX 6.48 5.50 6.20 9.60
DIM A B	MIN 6.40 5.10 5.80	MAX 6.48 5.50 6.20
DIM A B C D	MIN 6.40 5.10 5.80 9.20 2.20	MAX 6.48 5.50 6.20 9.60 2.40
DIM A B C D E	MIN 6.40 5.10 5.80 9.20 2.20 0.50	MAX 6.48 5.50 6.20 9.60 2.40 0.70
DIM A B C D E F	MIN 6.40 5.10 5.80 9.20 2.20 0.50 2.09	MAX 6.48 5.50 6.20 9.60 2.40 0.70 2.49
DIM A B C D E F G	MIN 6.40 5.10 5.80 9.20 2.20 0.50 2.09	MAX 6.48 5.50 6.20 9.60 2.40 0.70 2.49
DIM A B C D E F G H	m 6.40 5.10 5.80 9.20 2.20 0.50 2.09 2.09	MAX 6.48 5.50 6.20 9.60 2.40 0.70 2.49 2.49 0.60
DIM A B C D E F G	MIN 6.40 5.10 5.80 9.20 2.20 0.50 2.09	MAX 6.48 5.50 6.20 9.60 2.40 0.70 2.49



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2SC3518

ELECTRICAL CHARACTERISTICS

 T_{C} =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)} NOTE	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 200mA			0.3	V
V _{BE(sat)} NOTE	Base-Emitter Saturation Voltage	I _C = 2A; I _B = 200mA			1.2	V
Ісво	Collector Cutoff Current	V _{CB} = 50V; I _E = 0			10	μА
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μА
h _{FE-1} NOTE	DC Current Gain	I _C = 5A; V _{CE} = 1V	50			
h _{FE-2} NOTE	DC Current Gain	I _C = 2A; V _{CE} = 1V	100		400	
f _T NOTE	Current-Gain—Bandwidth Product	I _C = 500mA; V _{CE} = 10V		120		MHz

NOTE:Pulse test PW≤350us,duty cycle ≤2%/pulse

♦ h_{FE-2} Classifications

М	L	К		
100-200	160-320	200-400		

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